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THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent of : Attn: Certificate of  
Correction Branch

Tetsuya MATSUTANI :

Patent No. 7,316,972 : Atty Docket No. 2003\_1039A

Issued January 8, 2008 :

Confirmation No. 7670

CONTACT HOLE FORMATION METHOD

Certificate  
FEB 13 2008  
of Correction

**REQUEST FOR CERTIFICATE OF CORRECTION UNDER 37 CFR 1.322**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

THE COMMISSIONER IS AUTHORIZED  
TO CHARGE ANY DEFICIENCY IN THE  
FEES FOR THIS PAPER TO DEPOSIT  
ACCOUNT NO. 23-0975

Sir:

In accordance with the provisions of 37 CFR 1.322, it is respectfully requested that a  
Certificate of Correction issue to correct the following:

In claim 13, column 12, lines 22-52, claim 13 should read as follows,

--A method for forming a semiconductor device comprising:

forming a first group of interconnections on a first region of a substrate so that the first  
group of interconnections are densely arranged;

forming a second group of interconnections on a second region of the substrate so that the  
second group of interconnections are sparsely arranged;

forming a first dielectric film on the substrate;

planarizing the first dielectric film;

forming a second dielectric film on the first dielectric film, the second dielectric film  
having an etching rate different from an etching rate of the first dielectric film; and then

forming contact holes to a uniform depth through the first dielectric film and the second  
dielectric film,

wherein an entire surface of the first dielectric film is continuous and higher than a top  
surface of the interconnections just prior to planarizing the first dielectric film, and

wherein planarizing the first dielectric film results in the first dielectric film having a  
uniform thickness at those portions through which said contact holes are formed.--

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In claim 9, column 12, line 10, "pf" should be --of--.

In claim 29, column 13, line 50, "than the the etching" should be --than the etching--.

In claim 36, column 14, line 28, "notride" should be --nitride--.

In claim 57, column 16, line 4, "difernt" should be --different--.

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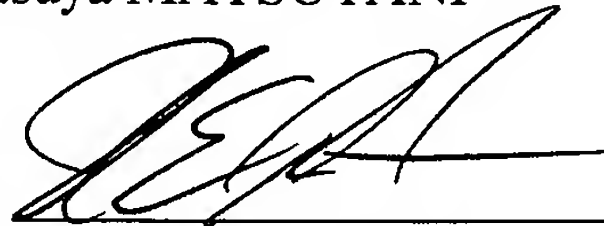
**REMARKS**

Each of the errors listed above apparently arose due to PTO mistakes. Accordingly, a Certificate of Correction should issue at no expense to patentee. Form PTO-1050 accompanies this request.

Respectfully submitted,

Tetsuya MATSUTANI

By



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February 13, 2008

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To: The Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450

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DATED : January 8, 2008  
INVENTOR(S) : Tetsuya MATSUTANI

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forming a second group of interconnections on a second region of the substrate so that the second group of interconnections are sparsely arranged;

forming a first dielectric film on the substrate;

planarizing the first dielectric film;

forming a second dielectric film on the first dielectric film, the second dielectric film having an etching rate different from an etching rate of the first dielectric film; and then

forming contact holes to a uniform depth through the first dielectric film and the second dielectric film,

wherein an entire surface of the first dielectric film is continuous and higher than a top surface of the interconnections just prior to planarizing the first dielectric film, and

wherein planarizing the first dielectric film results in the first dielectric film having a uniform thickness at those portions through which said contact holes are formed.--.

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